

SPECIFICATION OF INFRARED LED CHIP

C910-35

[INFRARED]

1) Commodity Type and Physical Characteristics.

- 1. Material GaAlAs
- 2. Electrode Top Side N ( cathode )side : Au Alloy  
Bottom Side P ( anode )side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA		1.30	1.45	V
Reverse Current	I <sub>r</sub>	V <sub>r</sub> =5V			10	uA
Power Intensity	P <sub>o</sub>	I <sub>f</sub> =20mA	1.0	2.0		mW
Peak Wavelength	λ <sub>p</sub>	I <sub>f</sub> =20mA	900	910	920	nm
Spectral Radiation Bandwidth	Δλ	I <sub>f</sub> =20mA		45		nm
RiseTime	t <sub>r</sub>	I <sub>f</sub> =20mA		1000		ns
FallTime	t <sub>f</sub>	I <sub>f</sub> =20mA		800		ns

‡Die shall be mounted on TO-18 gold header without resin coated.(Ta=25°C)

[Unit : um]

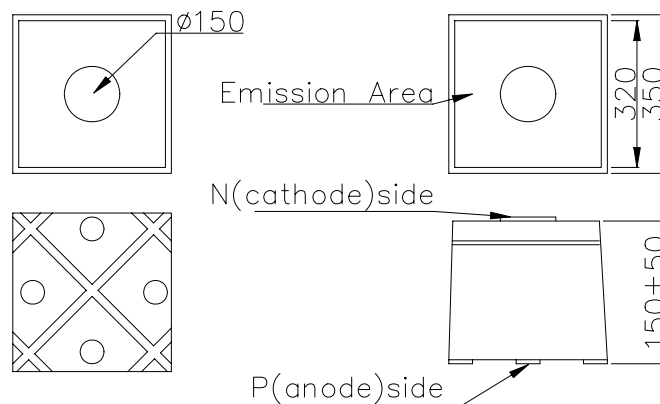


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area